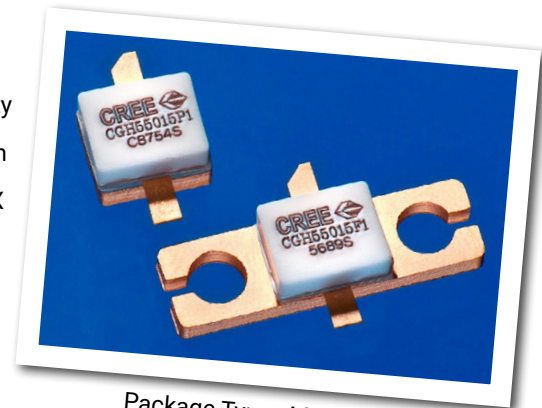


# CGH55015F1 / CGH55015P1

15 W, 5500-5800 MHz, GaN HEMT for WiMAX

Cree's CGH55015F1/CGH55015P1 is a gallium nitride (GaN) high electron mobility transistor (HEMT) designed specifically for high efficiency, high gain and wide bandwidth capabilities, which makes the CGH55015F1/CGH55015P1 ideal for 5.5-5.8 GHz WiMAX and linear amplifier applications. The transistor is available in both screw-down, flange and solder-down, pill packages. Based on appropriate external match adjustment, the CGH55015F1/CGH55015P1 is suitable for 4.9 - 5.5 GHz applications as well.



Package Type: 440196 & 440166  
PN: CGH55015P1 & CGH55015F1

## Typical Performance 5.5-5.8GHz ( $T_c = 25^\circ\text{C}$ )

Parameter	5.50 GHz	5.65 GHz	5.80 GHz	Units
Small Signal Gain	10.7	11.0	10.7	dB
EVM at $P_{AVE} = 23$ dBm	1.9	1.8	2.0	%
EVM at $P_{AVE} = 33$ dBm	1.5	1.5	1.7	%
Drain Efficiency at $P_{AVE} = 33$ dBm	25	25	25	%
Input Return Loss	11.5	14.5	10.5	dB

**Note:**

Measured in the CGH55015-AMP amplifier circuit, under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

## Features



- 5.5 - 5.8 GHz Operation
- 15 W Peak Power Capability
- >10.5 dB Small Signal Gain
- 2 W  $P_{AVE} < 2.0$  % EVM
- 25 % Efficiency at 2 W Average Power
- Designed for WiMAX Fixed Access 802.16-2004 OFDM Applications
- Designed for Multi-carrier DOCSIS Applications

Large Signal Models Available for ADS and MWO

## Absolute Maximum Ratings (not simultaneous) at 25°C Case Temperature

Parameter	Symbol	Rating	Units	Conditions
Drain-Source Voltage	$V_{DSS}$	84	Volts	25°C
Gate-to-Source Voltage	$V_{GS}$	-10, +2	Volts	25°C
Power Dissipation	$P_{DISS}$	7	Watts	
Storage Temperature	$T_{STG}$	-65, +150	°C	
Operating Junction Temperature	$T_J$	225	°C	
Maximum Forward Gate Current	$I_{GMAX}$	4.0	mA	25°C
Maximum Drain Current <sup>1</sup>	$I_{DMAX}$	1.5	A	25°C
Soldering Temperature <sup>2</sup>	$T_S$	245	°C	
Screw Torque	$\tau$	60	in-oz	
Thermal Resistance, Junction to Case <sup>3</sup>	$R_{\theta JC}$	8.0	°C/W	85°C
Case Operating Temperature <sup>3</sup>	$T_C$	-40, +150	°C	

Note:

<sup>1</sup> Current limit for long term, reliable operation.

<sup>2</sup> Refer to the Application Note on soldering at [www.cree.com/RF/Document-Library](http://www.cree.com/RF/Document-Library)

<sup>3</sup> Measured for the CGH55015 at  $P_{DISS} = 7W$ .

## Electrical Characteristics ( $T_C = 25^\circ C$ )

Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
<b>DC Characteristics<sup>1</sup></b>						
Gate Threshold Voltage	$V_{GS(th)}$	-3.8	-3.0	-2.3	$V_{DC}$	$V_{DS} = 10 V, I_D = 3.6 mA$
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	$V_{DC}$	$V_{DS} = 28 V, I_D = 115 mA$
Saturated Drain Current	$I_{DS}$	2.9	3.5	-	A	$V_{DS} = 6.0 V, V_{GS} = 2.0 V$
Drain-Source Breakdown Voltage	$V_{BR}$	120	-	-	$V_{DC}$	$V_{GS} = -8 V, I_D = 3.6 mA$
<b>RF Characteristics<sup>2,3</sup> (<math>T_C = 25^\circ C, F_0 = 5.65 GHz</math> unless otherwise noted)</b>						
Small Signal Gain	$G_{SS}$	8.5	11.0	-	dB	$V_{DD} = 28 V, I_{DQ} = 115 mA$
Drain Efficiency <sup>4</sup>	$\eta$	20.6	25	-	%	$V_{DD} = 28 V, I_{DQ} = 115 mA, P_{AVE} = 2.0 W$
Error Vector Magnitude	EVM	-	2.0	2.5	%	$V_{DD} = 28 V, I_{DQ} = 115 mA, P_{AVE} = 2.0 W$
Output Mismatch Stress	VSWR	-	-	10 : 1	$\Psi$	No damage at all phase angles, $V_{DD} = 28 V, I_{DQ} = 115 mA,$ $P_{AVE} = 2.0 W$
<b>Dynamic Characteristics</b>						
Input Capacitance	$C_{GS}$	-	4.5	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$
Output Capacitance	$C_{DS}$	-	1.3	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$
Feedback Capacitance	$C_{GD}$	-	0.2	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$

Notes:

<sup>1</sup> Measured on wafer prior to packaging.

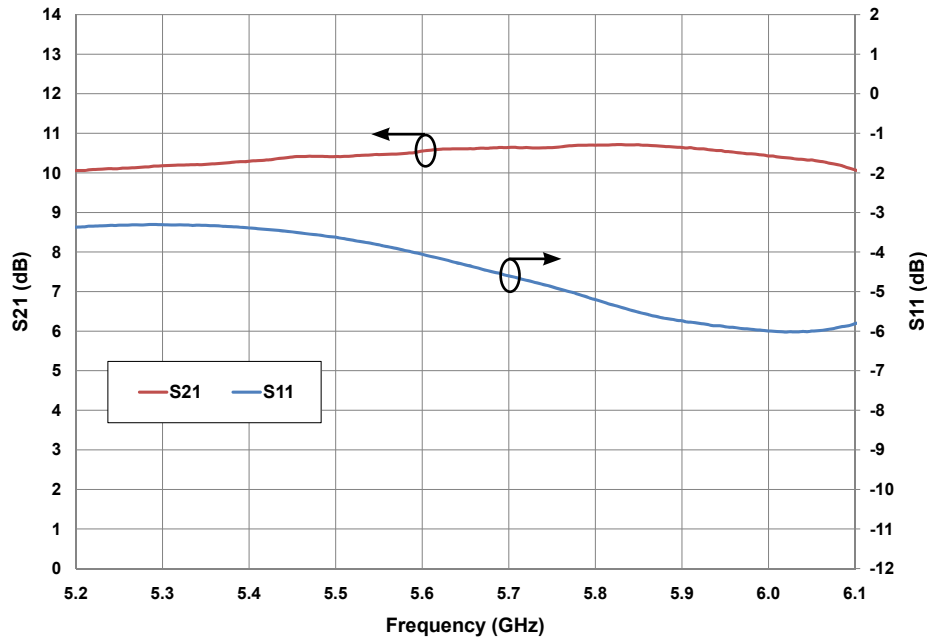
<sup>2</sup> Measured in the CGH55015-AMP test fixture.

<sup>3</sup> Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, 5 ms Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

<sup>4</sup> Drain Efficiency =  $P_{OUT} / P_{DC}$

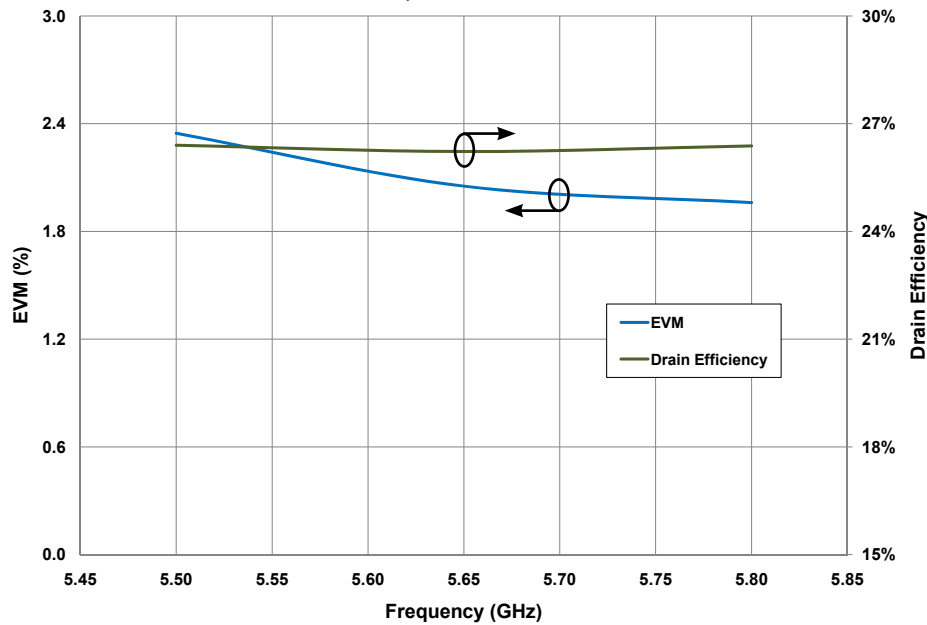
## Typical WiMAX Performance

**Small Signal S-Parameters vs Frequency measured  
in the CGH55015-AMP  
 $V_{DD} = 28\text{ V}, I_{DQ} = 115\text{ mA}$**



**EVM and Efficiency vs. Frequency measured  
in the CGH55015-AMP**

$V_{DD} = 28\text{ V}, I_{DQ} = 115\text{ mA}, P_{OUT} = 2.5\text{ W}$

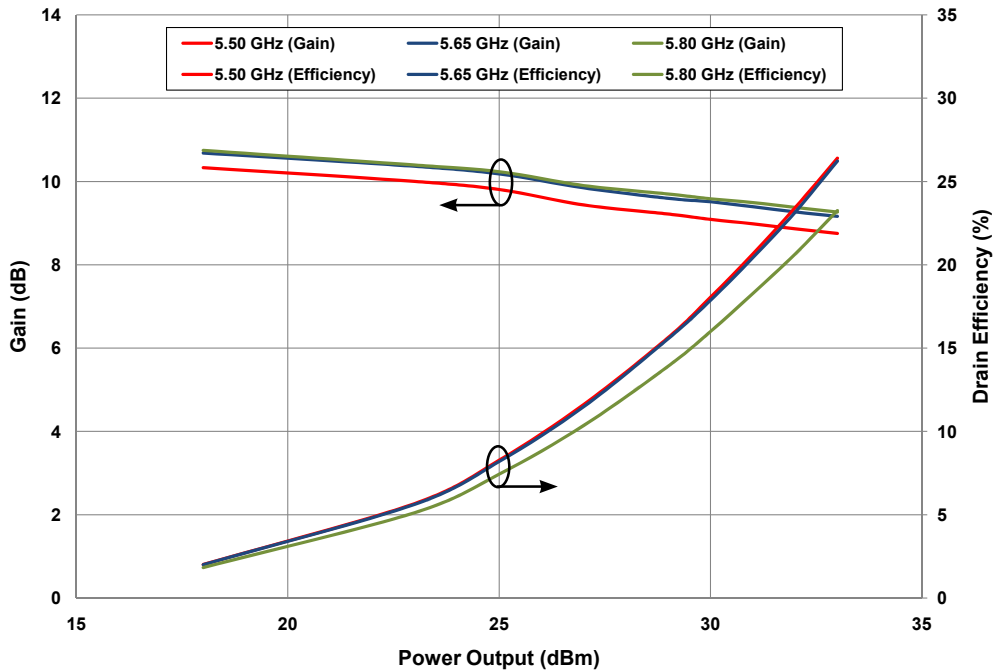


Note:

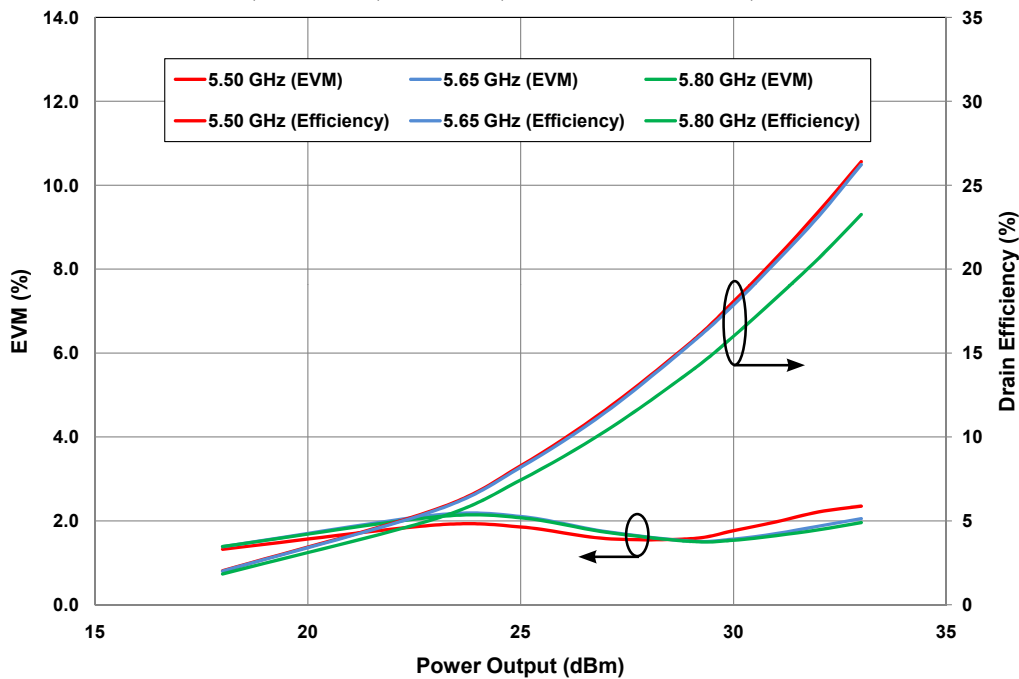
Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

## Typical WiMAX Performance

**Drain Efficiency and Gain vs Power Output measured in the CGH55015-AMP**  
 $V_{DD} = 28\text{ V}$ ,  $I_{DQ} = 115\text{ mA}$ , 802.16-2004 OFDM, PAR = 9.8 dB



**Typical EVM and Drain Efficiency vs Output Power measured in the CGH55015-AMP at 5.50 GHz, 5.65 GHz, 5.80 GHz, 802.16-2004 OFDM, PAR=9.8 dB**

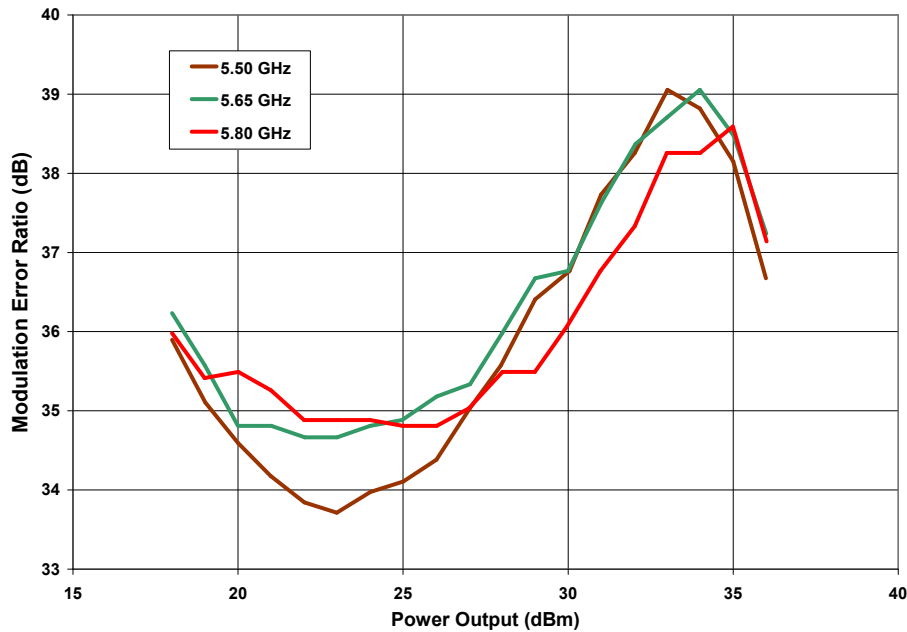


**Note:**

Under 802.16 OFDM, 3.5 MHz Channel BW, 1/4 Cyclic Prefix, 64 QAM Modulated Burst, Symbol Length of 59, Coding Type RS-CC, Coding Rate Type 2/3, PAR = 9.8 dB @ 0.01 % Probability on CCDF.

## Typical DOCSIS Performance

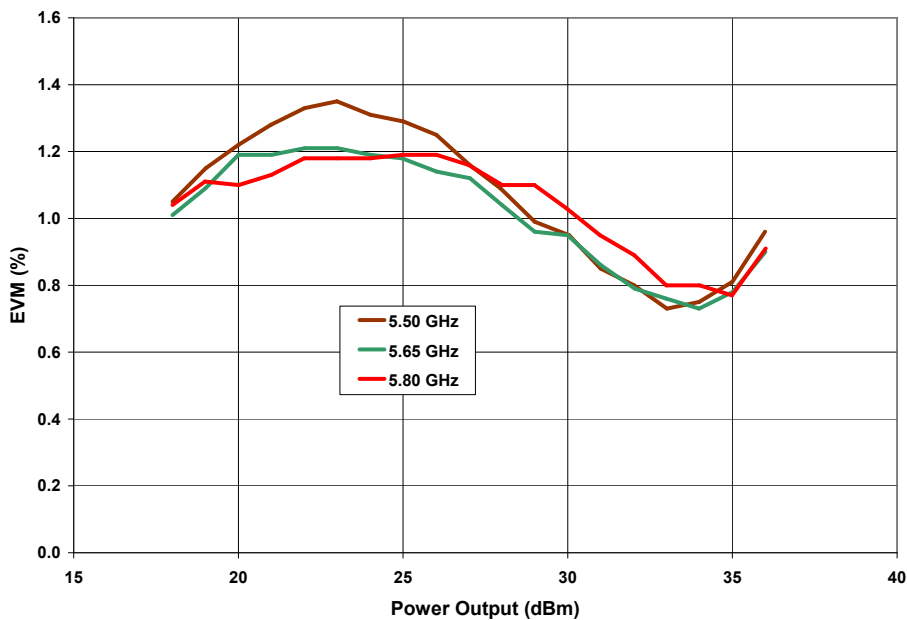
### DOCSIS Modulation Error Ratio vs Output Power of CGH55015



Note:

MER is the metric of choice for cable systems and can be related to EVM by the following equation:  $EVM(\%) = 100 \times 10^{-((MER_{dB} + MTA_{dB})/20)}$ . MTA is the "maximum-to-average constellation power ratio" which varies with the modulation type: MTA = 0 for BPSK and QPSK; 2.55 for 16QAM and 8QAM-DS; 3.68 for 64QAM and 32QAM-DS; 4.23 for 256QAM and 128QAM-DS

### DOCSIS EVM vs Output Power of CGH55015 in Broadband Amplifier Circuit

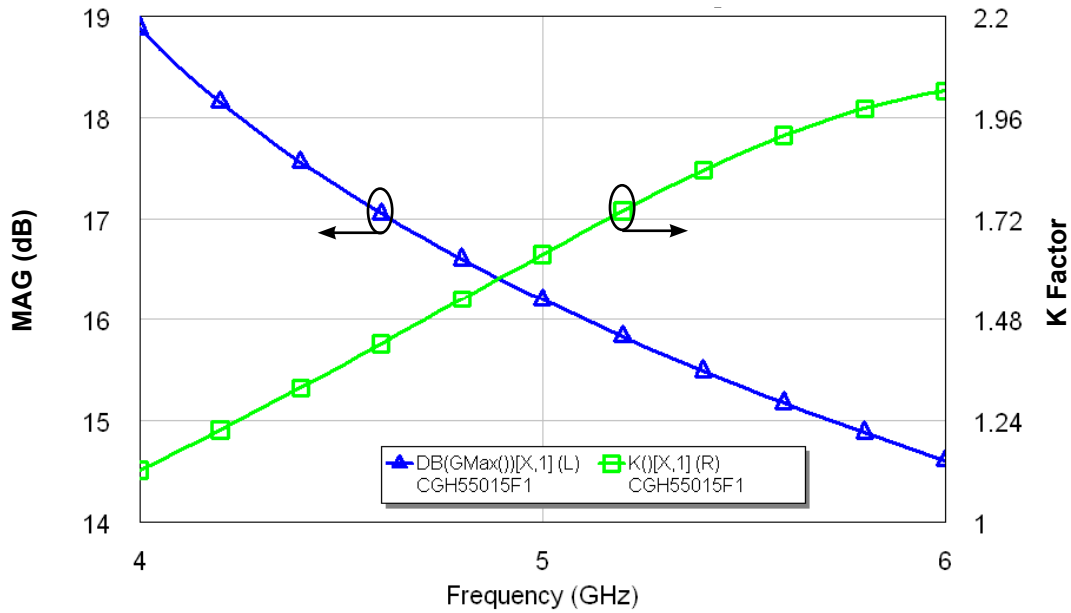


Note:

Under DOCSIS, 6.0 MHz Channel BW, 64 QAM, PN23, Filter Alpha 0.18, PAR = 6.7dB.

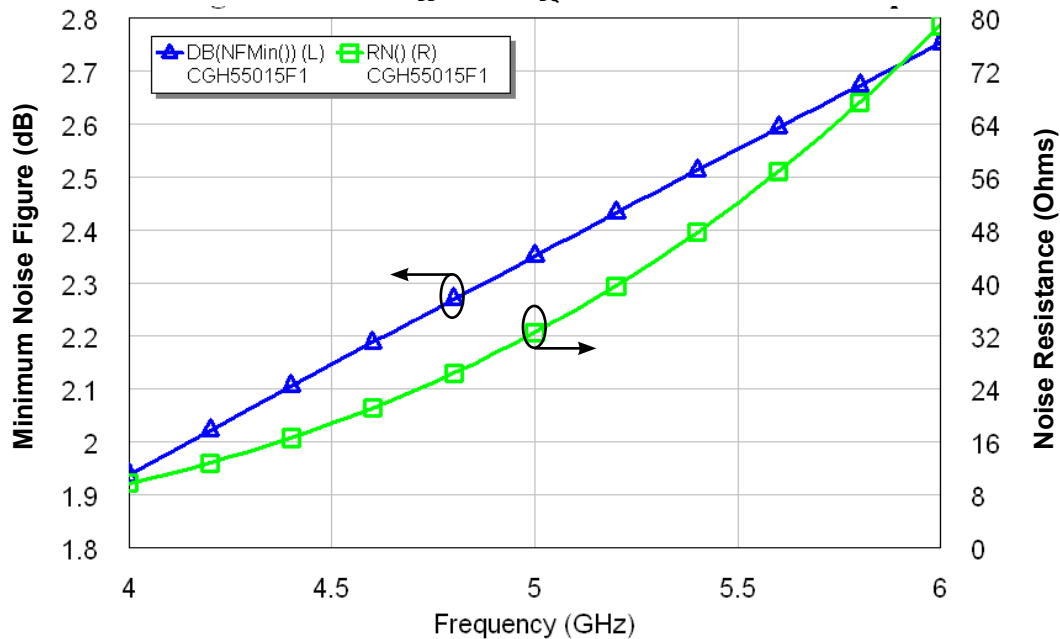
## Typical Performance

**Simulated Maximum Available Gain and K Factor of the CGH55015F1/P1**  
 $V_{DD} = 28\text{ V}, I_{DQ} = 115\text{ mA}$

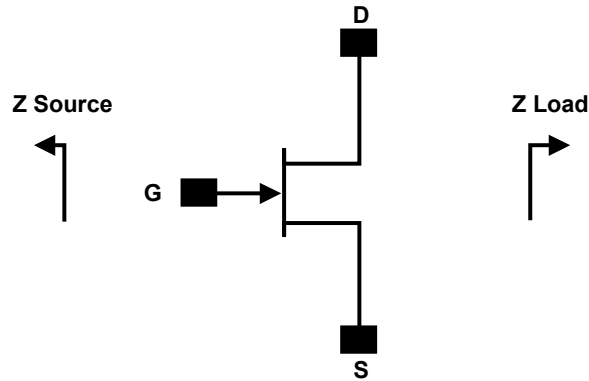


## Typical Noise Performance

**Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH55015F1/P1**  
 $V_{DD} = 28\text{ V}, I_{DQ} = 115\text{ mA}$



## Source and Load Impedances



Frequency (MHz)	Z Source	Z Load
5500	8.7 - j30.2	21.6 - j4.7
5650	10.2 - j26.9	24.2 - j5.5
5800	12.3 - j24.3	26.5 - j7.5

Note 1.  $V_{DD} = 28V$ ,  $I_{DQ} = 115$  mA in the 440166 package.

Note 2. Impedances are extracted from the CGH55015-AMP demonstration amplifier and are not source and load pull data derived from the transistor.

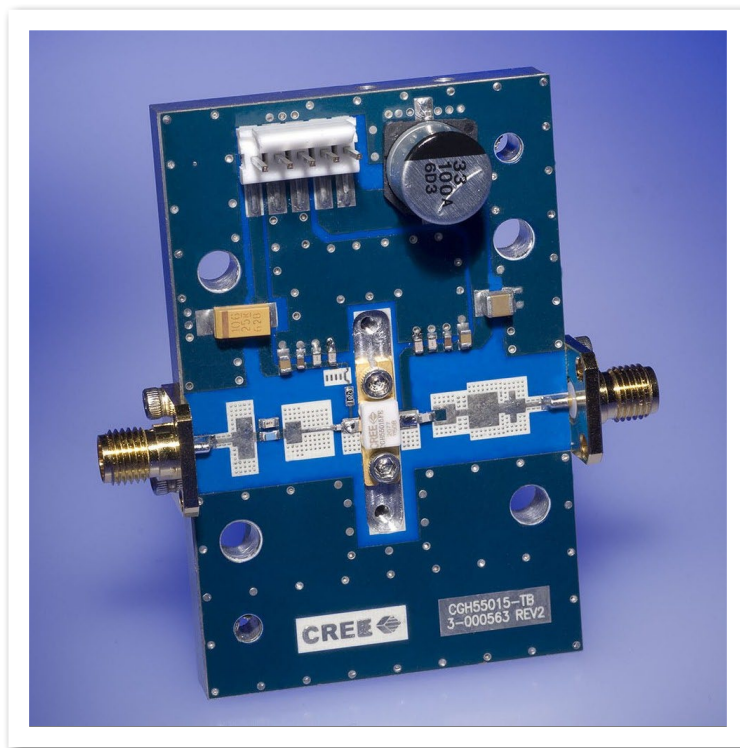
## Electrostatic Discharge (ESD) Classifications

Parameter	Symbol	Class	Test Methodology
Human Body Model	HBM	1A > 250 V	JEDEC JESD22 A114-D
Charge Device Model	CDM	1 < 200 V	JEDEC JESD22 C101-C

## CGH55015-AMP1 Demonstration Amplifier Circuit Bill of Materials

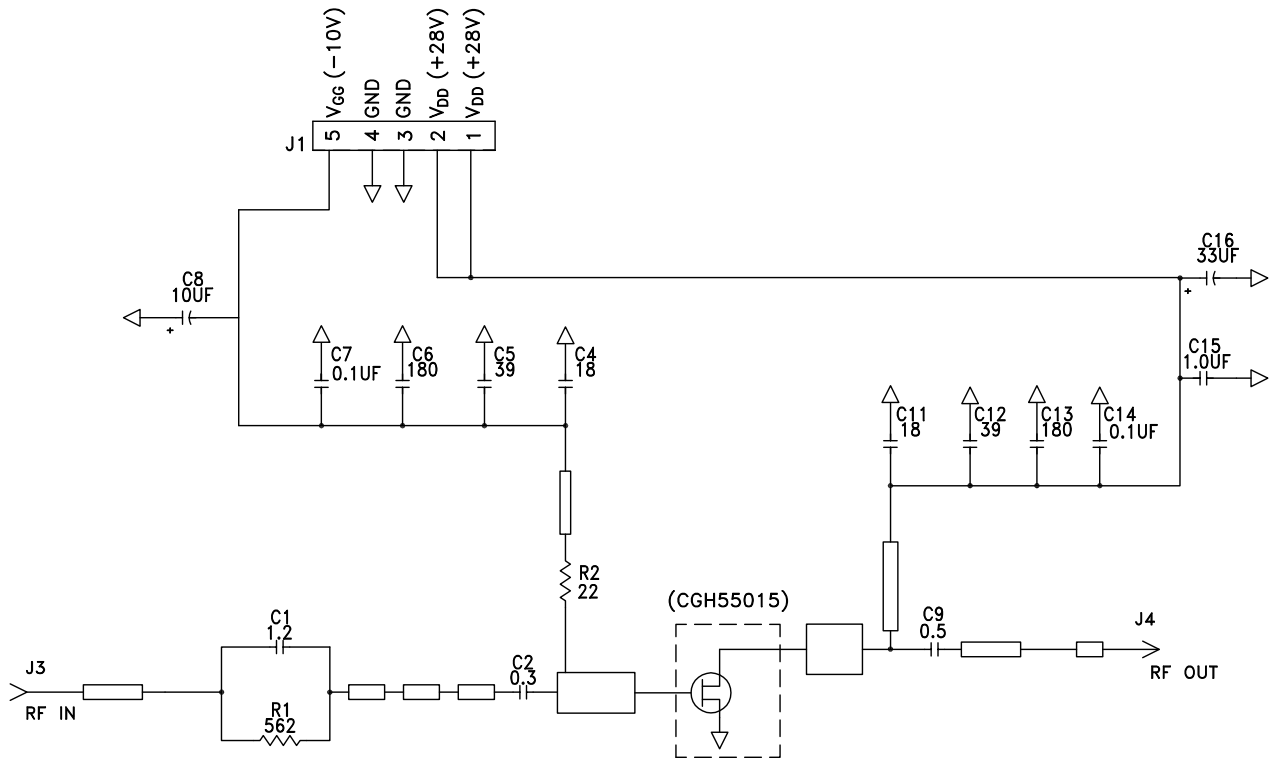
Designator	Description	Qty
C1	CAP, 1.2pF, +/-0.1 pF, 0603, ATC 600S	1
C2	CAP, 0.3pF, +/-0.05 pF, 0402, ATC 600L	1
C9	CAP, 0.5pF,+/-0.05pF, 0603, ATC 600S	1
C4,C11	CAP, 18pF, +/-5%, 0603, ATC 600S	2
C5,C12	CAP, 39pF +/-5%, 0603, ATC 600S	2
C6,C13	CAP, CER, 180pF, 50V, +/-5%, C0G, 0603	2
C7,C14	CAP, CER, 0.1UF, 50V, +/-10%, X7R, 0805	2
C8	CAP, 10UF, 16V, SMT, TANTALUM	1
C15	CAP, 1.0UF ±10%, 100V, 1210, X7R	1
C16	CAP, 33UF, 100V, ELECT, FK, SMD	1
R1	RES, 1/16W, 0603, 1%, 562 OHMS	1
R2	RES, 1/16W, 0603, 1%, 22 OHMS	1
J1	HEADER RT> PLZ .1 CEN LK 5 POS	1
J3,J4	CONN, SMA, FLANGE	2
-	PCB, RO4350B, Er = 3.48, h = 20 mil	1
-	CGH55015	1

## CGH55015-AMP Demonstration Amplifier Circuit

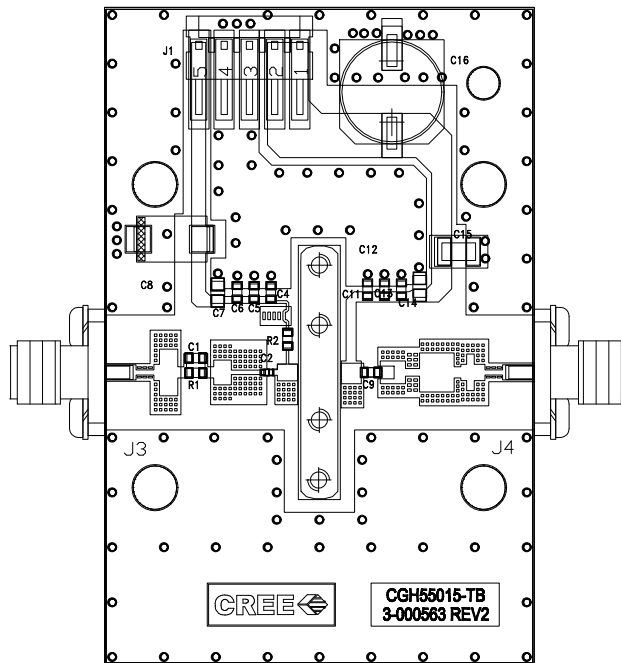




## CGH55015-AMP Demonstration Amplifier Circuit Schematic



## CGH55015-AMP Demonstration Amplifier Circuit Outline

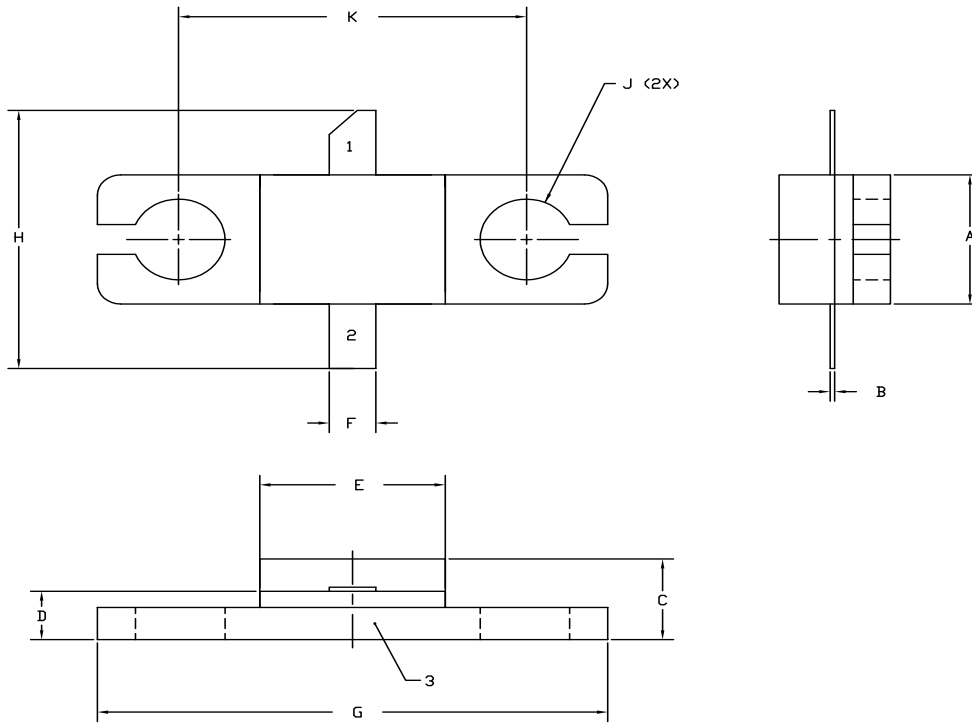


**Typical Package S-Parameters for CGH55015**  
 (Small Signal,  $V_{DS} = 28\text{ V}$ ,  $I_{DQ} = 115\text{ mA}$ , angle in degrees)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.909	-125.16	17.56	107.52	0.026	20.86	0.330	-95.81
600 MHz	0.903	-134.72	15.15	101.24	0.027	15.25	0.318	-103.71
700 MHz	0.898	-142.24	13.28	95.96	0.027	10.66	0.312	-109.87
800 MHz	0.895	-148.34	11.79	91.38	0.027	6.76	0.309	-114.77
900 MHz	0.893	-153.43	10.58	87.30	0.028	3.37	0.310	-118.75
1.0 GHz	0.891	-157.78	9.59	83.58	0.028	0.34	0.312	-122.07
1.2 GHz	0.889	-164.93	8.06	76.89	0.028	-4.92	0.320	-127.35
1.4 GHz	0.888	-170.72	6.94	70.90	0.027	-9.46	0.332	-131.53
1.6 GHz	0.888	-175.64	6.08	65.34	0.027	-13.51	0.347	-135.09
1.8 GHz	0.888	-179.99	5.41	60.10	0.027	-17.20	0.362	-138.30
2.0 GHz	0.889	176.04	4.86	55.09	0.026	-20.60	0.378	-141.33
2.2 GHz	0.889	172.35	4.42	50.24	0.025	-23.76	0.394	-144.27
2.4 GHz	0.890	168.84	4.05	45.53	0.025	-26.70	0.410	-147.16
2.6 GHz	0.891	165.46	3.73	40.93	0.024	-29.44	0.426	-150.04
2.8 GHz	0.891	162.16	3.46	36.41	0.024	-31.97	0.441	-152.92
3.0 GHz	0.892	158.90	3.23	31.95	0.023	-34.32	0.455	-155.81
3.2 GHz	0.893	155.67	3.03	27.55	0.022	-36.45	0.469	-158.73
3.4 GHz	0.893	152.43	2.85	23.19	0.021	-38.38	0.482	-161.68
3.6 GHz	0.894	149.18	2.70	18.85	0.021	-40.07	0.494	-164.66
3.8 GHz	0.894	145.89	2.56	14.53	0.020	-41.52	0.506	-167.68
4.0 GHz	0.894	142.54	2.44	10.22	0.019	-42.71	0.516	-170.74
4.1 GHz	0.895	140.85	2.38	8.07	0.019	-43.19	0.521	-172.29
4.2 GHz	0.895	139.14	2.33	5.91	0.019	-43.59	0.526	-173.85
4.3 GHz	0.895	137.40	2.28	3.75	0.018	-43.92	0.530	-175.43
4.4 GHz	0.895	135.65	2.23	1.58	0.018	-44.16	0.535	-177.02
4.5 GHz	0.895	133.88	2.18	-0.59	0.018	-44.32	0.539	-178.62
4.6 GHz	0.895	132.08	2.14	-2.77	0.017	-44.38	0.543	179.75
4.7 GHz	0.895	130.26	2.10	-4.96	0.017	-44.35	0.546	178.11
4.8 GHz	0.895	128.41	2.06	-7.15	0.017	-44.23	0.550	176.45
4.9 GHz	0.895	126.53	2.03	-9.36	0.017	-44.02	0.553	174.77
5.0 GHz	0.895	124.63	1.99	-11.58	0.016	-43.71	0.556	173.07
5.1 GHz	0.895	122.69	1.96	-13.81	0.016	-43.30	0.559	171.35
5.2 GHz	0.895	120.72	1.93	-16.05	0.016	-42.81	0.561	169.60
5.3 GHz	0.895	118.73	1.90	-18.31	0.016	-42.22	0.564	167.83
5.4 GHz	0.895	116.70	1.87	-20.59	0.016	-41.56	0.566	166.04
5.5 GHz	0.895	114.63	1.84	-22.89	0.016	-40.83	0.568	164.21
5.6 GHz	0.895	112.53	1.81	-25.20	0.016	-40.05	0.570	162.36
5.7 GHz	0.895	110.39	1.79	-27.53	0.016	-39.22	0.572	160.47
5.8 GHz	0.895	108.22	1.77	-29.89	0.016	-38.35	0.574	158.55
5.9 GHz	0.895	106.00	1.74	-32.27	0.016	-37.48	0.575	156.60
6.0 GHz	0.895	103.75	1.72	-34.67	0.016	-36.62	0.576	154.61

To download the s-parameters in s2p format, go to the [CGH55015F1/P1 Product Page](#), click on the documentation tab.

## Product Dimensions CGH55015F1 (Package Type – 440166)



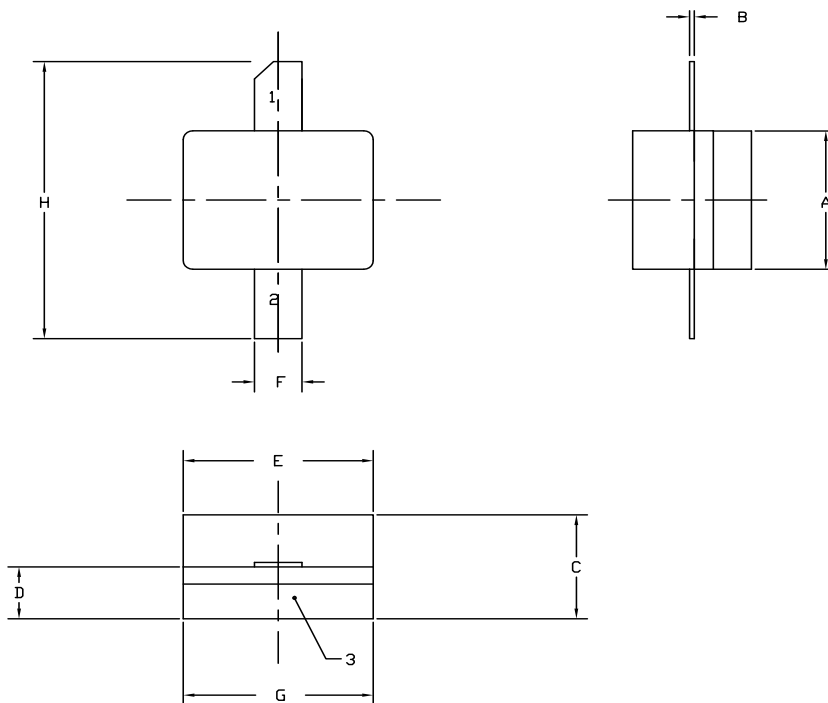
**NOTES:**

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. ADHESIVE FROM LID MAY EXTEND A MAXIMUM OF 0.020" BEYOND EDGE OF LID.
4. LID MAY BE MISALIGNED TO THE BODY OF THE PACKAGE BY A MAXIMUM OF 0.008" IN ANY DIRECTION.
5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.004	0.006	0.10	0.15
C	0.115	0.135	2.92	3.43
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.545	0.555	13.84	14.09
H	0.280	0.360	7.11	9.14
J	$\phi$ .100		2.54	
K	0.375		9.53	

PIN 1. GATE  
PIN 2. DRAIN  
PIN 3. SOURCE

## Product Dimensions CGH55015P1 (Package Type – 440196)



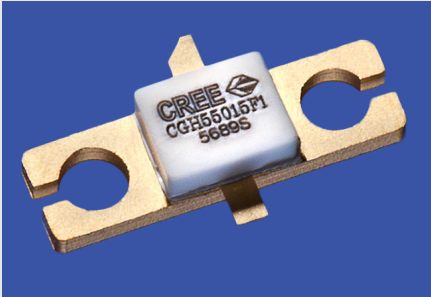
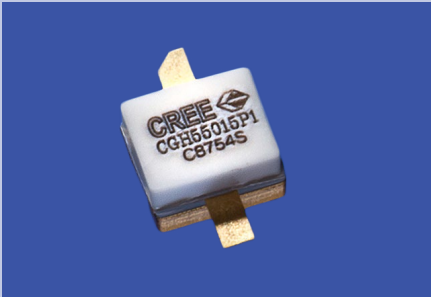
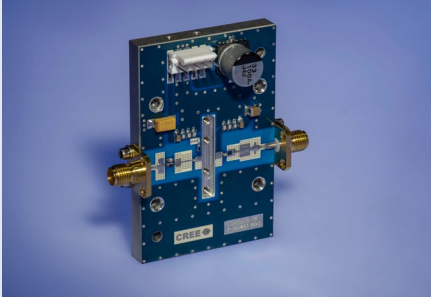
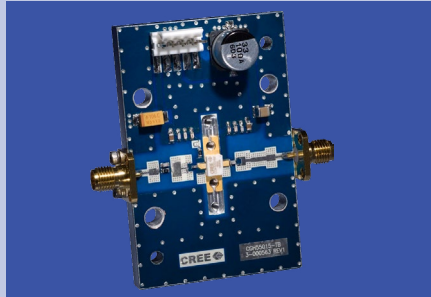
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5. ALL PLATED SURFACES ARE NI/AU

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.155	0.165	3.94	4.19
B	0.003	0.006	0.10	0.15
C	0.115	0.135	2.92	3.17
D	0.057	0.067	1.45	1.70
E	0.195	0.205	4.95	5.21
F	0.045	0.055	1.14	1.40
G	0.195	0.205	4.95	5.21
H	0.280	0.360	7.11	9.14

PIN 1. GATE  
PIN 2. DRAIN  
PIN 3. SOURCE

## Product Ordering Information

Order Number	Description	Unit of Measure	Image
CGH55015F1	GaN HEMT	Each	
CGH55015P1	GaN HEMT	Each	
CGH55015-TB	Test board without GaN HEMT	Each	
CGH55015-AMP	Test board with GaN HEMT installed	Each	



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